

SK8603150L

Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : $R_{DS(on)}$ typ = 2.5 m Ω (VGS = 4.5 V)
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : 15

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

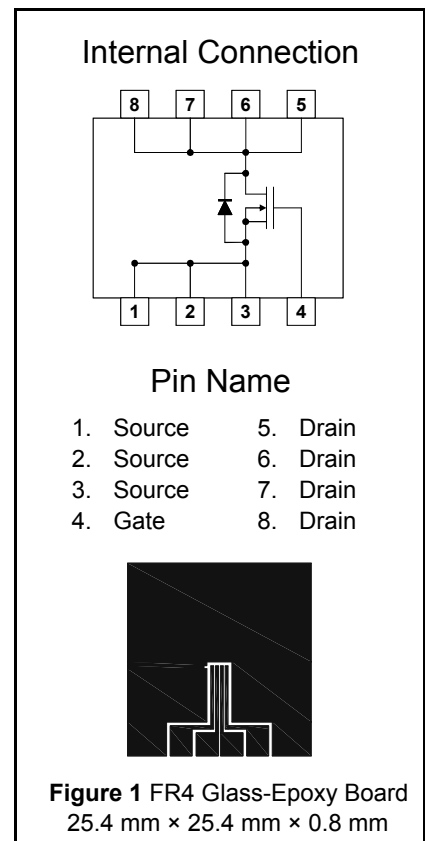
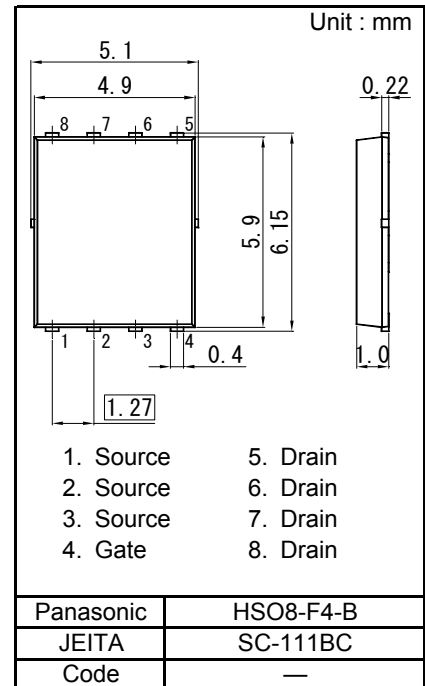
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit	
Drain to Source Voltage	VDS	30	V	
Gate to Source Voltage	VGS	±20		
Drain Current	ID	Ta = 25 °C, t = 10 s ^{*1}	40	A
		Ta = 25 °C, DC ^{*1}	26	
		Tc = 25 °C	89	
		Pulsed, Tch < 150 °C ^{*2}	120	
Total Power Dissipation	PD	Ta = 25 °C, DC ^{*1}	2.9	W
		Tc = 25 °C	34	
Thermal Resistance	Channel to Ambient	Rth(ch-a)	42	°C / W
	Channel to Case	Rth(ch-c)	3.7	
Channel Temperature	Tch	150	°C	
Operating ambient temperature	Topr	-40 to +85		
Storage Temperature Range	Tstg	-55 to +150		
Avalanche Current (Single pulse) ^{*3}	IAR	20	A	
Avalanche Energy (Single pulse) ^{*3}	EAR	46	mJ	

Note *1 Device mounted on a glass-epoxy board in Figure 1

*2 Pulse test: Ensure that the channel temperature does not exceed 150 °C

*3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 °C (initial)



■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = 4.38 mA, VDS = 10 V	1.3		3	V
Drain-source On-state Resistance	RDS(on)1	ID = 20 A, VGS = 10 V		1.9	2.5	mΩ
	RDS(on)2	ID = 20 A, VGS = 4.5 V		2.5	3.5	

Dynamic Characteristics

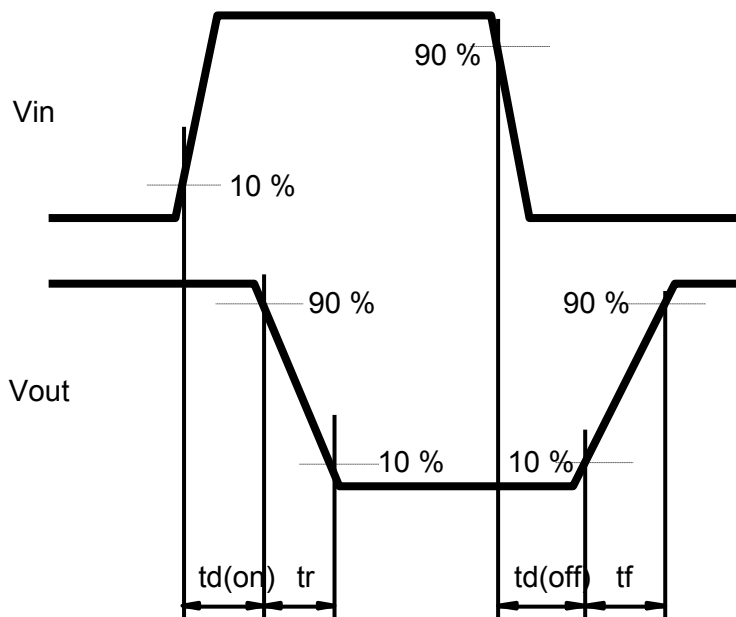
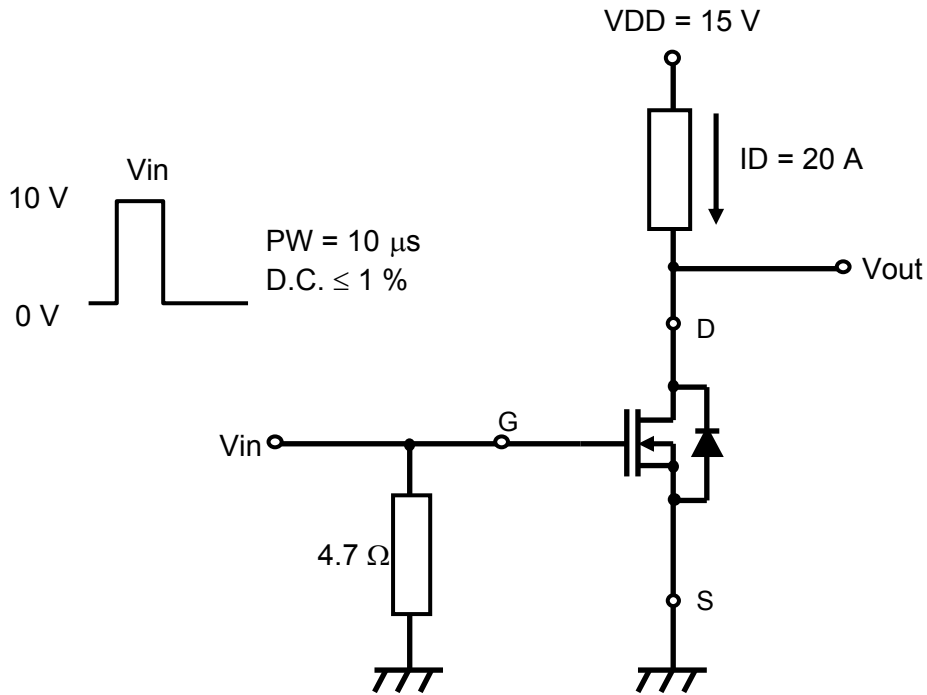
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		3 700	5 180	pF
Output Capacitance	Coss			430	602	
Reverse Transfer Capacitance	Crss			310	496	
Turn-on Delay Time ^{*1}	td(on)	VDD = 15 V, VGS = 0 to 10 V		13		ns
Rise Time ^{*1}	tr	ID = 20 A		14		
Turn-off Delay Time ^{*1}	td(off)	VDD = 15 V, VGS = 10 to 0 V		64		ns
Fall Time ^{*1}	tf	ID = 20 A		9		
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V ID = 20 A		28		nC
Gate to Source Charge	Qgs			9		
Gate to Drain Charge	Qgd			10		
Gate resistance	rg	f = 5 MHz		0.8	3	Ω

Body Diode Characteristic

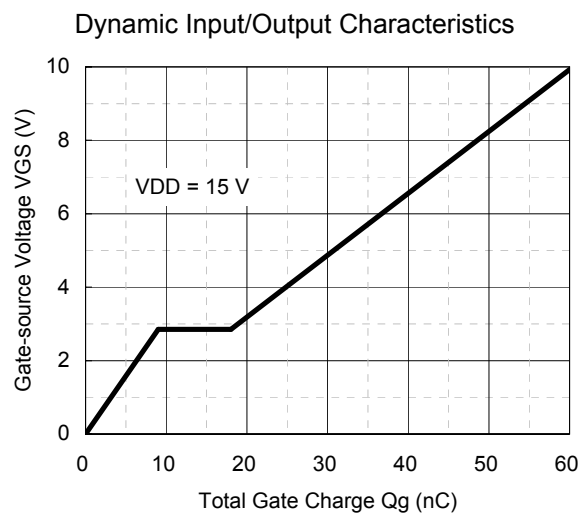
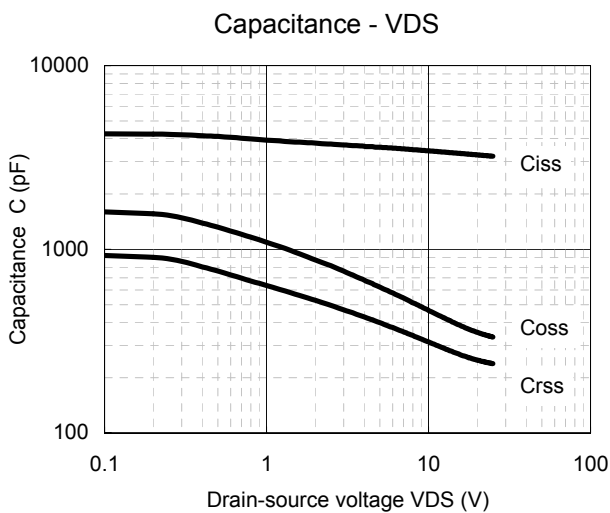
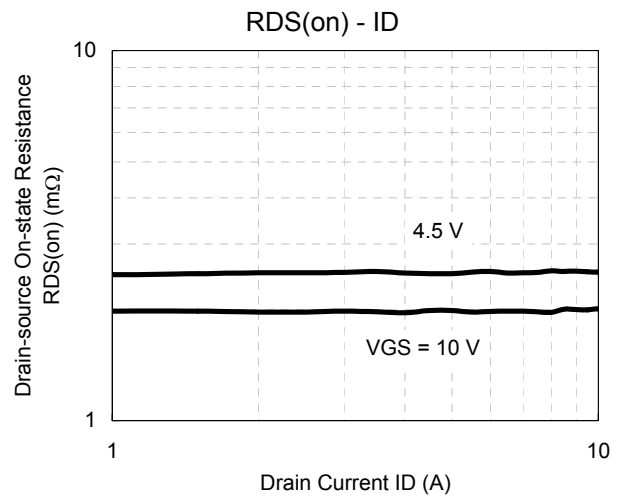
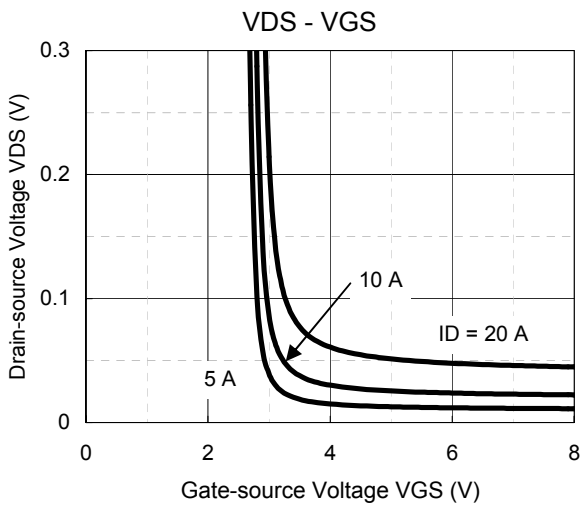
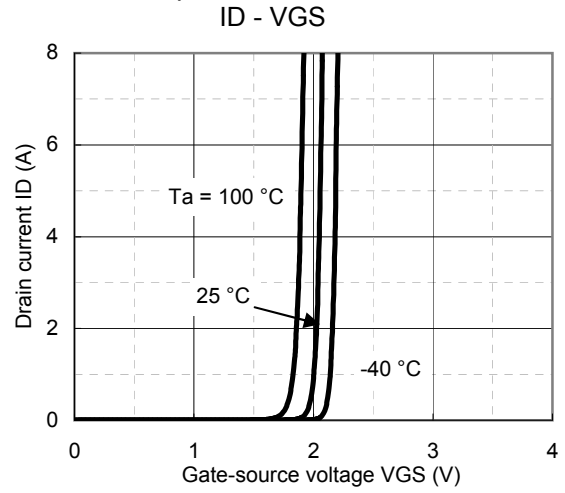
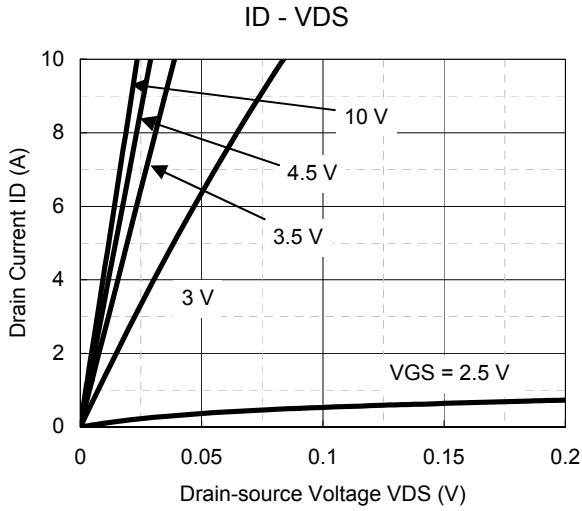
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	VSD	IS = 20 A, VGS = 0 V		0.9	1.2	V

Note : 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.
2. *1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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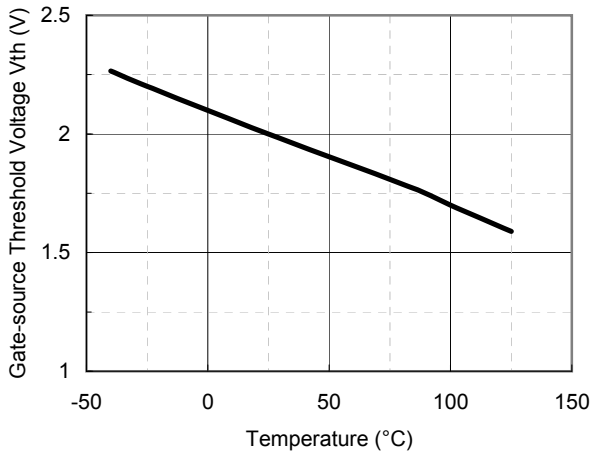


Technical Data (reference)

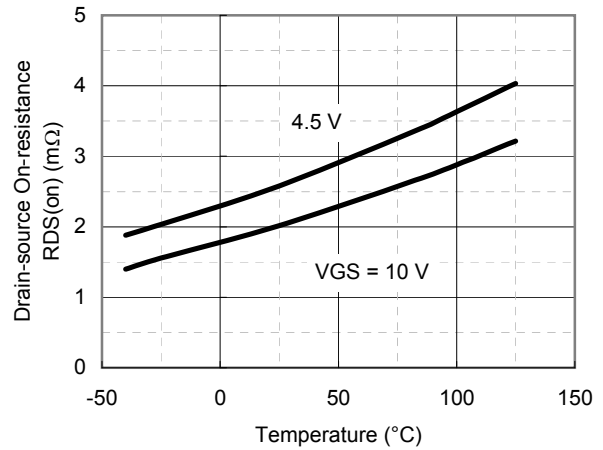


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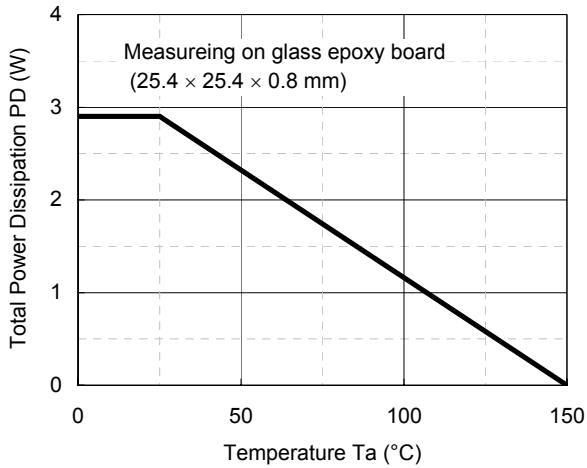
Vth - Ta



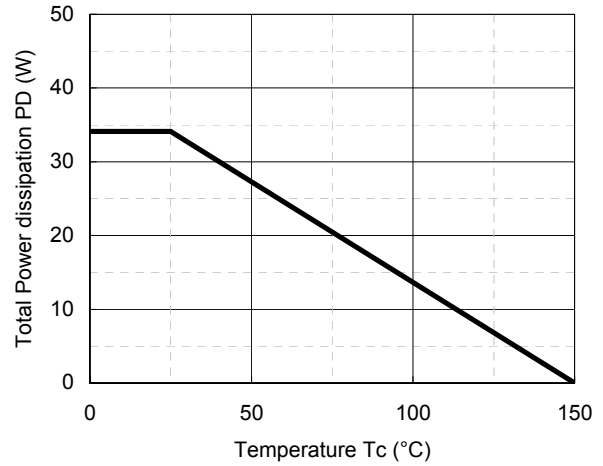
RDS(on) - Ta



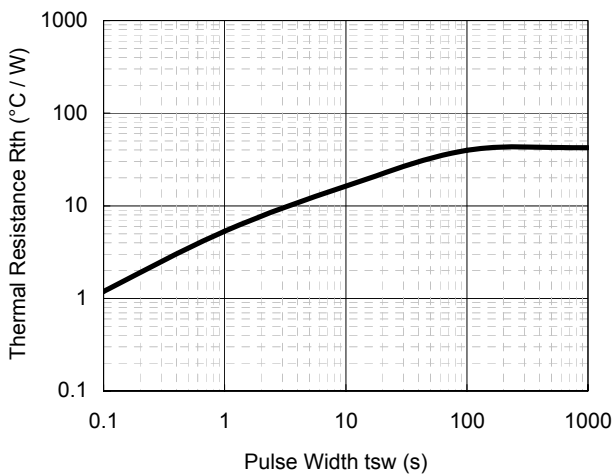
PD - Ta



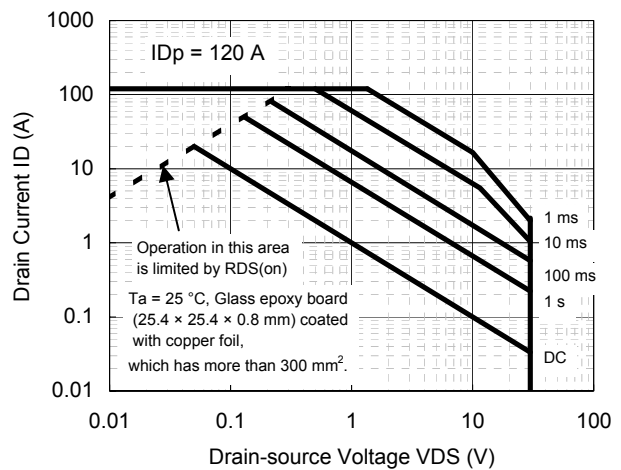
PD - Tc



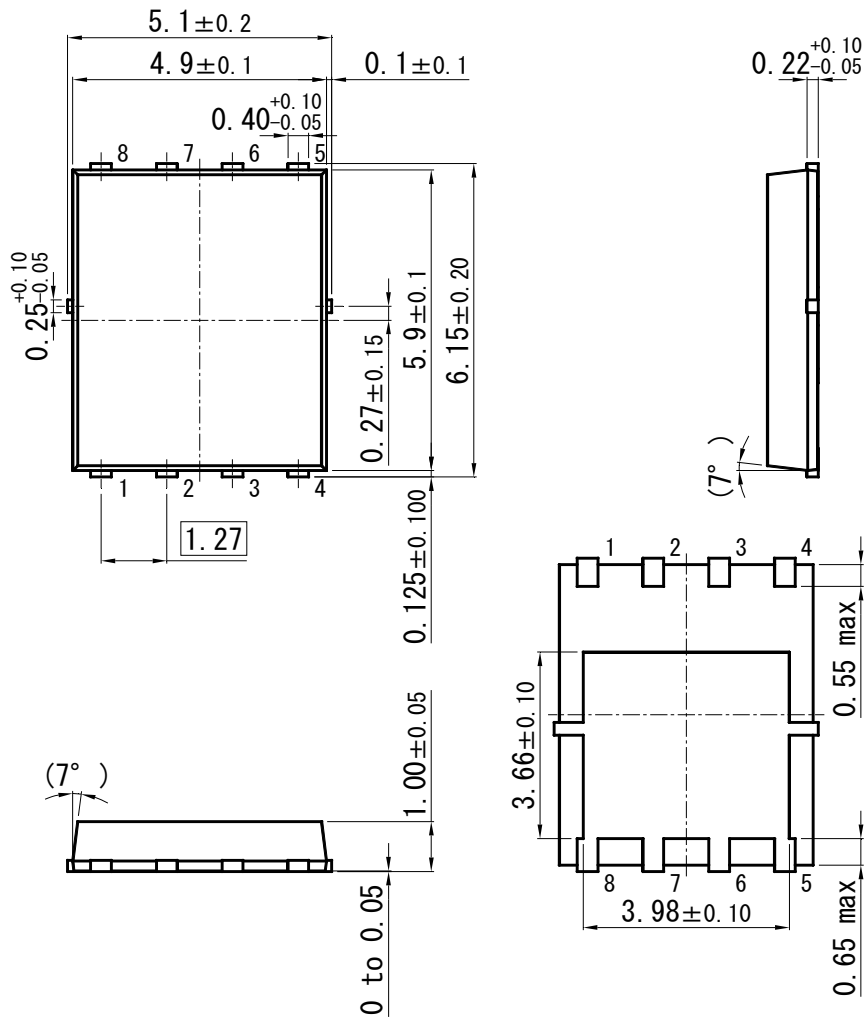
Rth - tsw



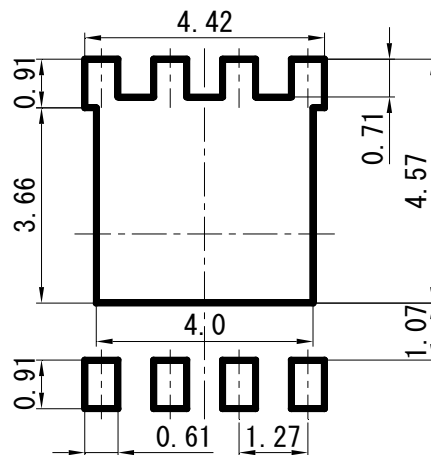
Safe Operating Area



HSO8-F4-B



■ Land Pattern (Reference) (Unit : mm)



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